

Silicon NPN Power Transistors

2SC2682

DESCRIPTION

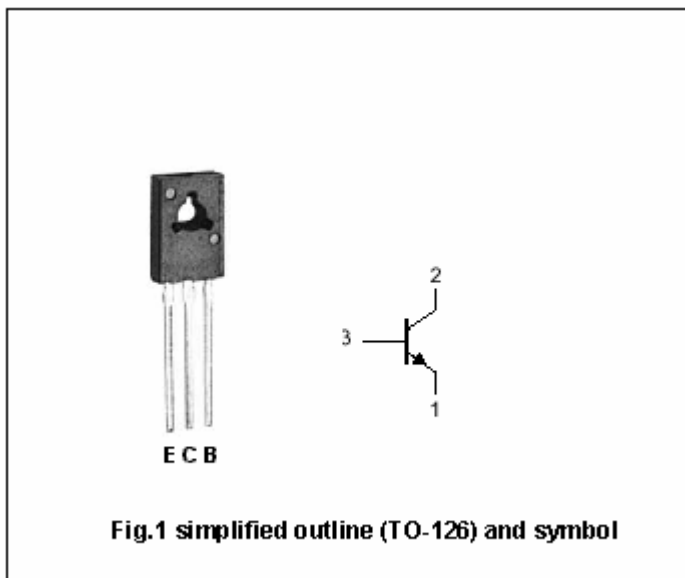
- With TO-126 package
- Complement to type 2SA1142

APPLICATIONS

- Audio frequency power amplifier; high frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	180	V
V _{CEO}	Collector-emitter voltage	Open base	180	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		0.1	A
P _C	Collector power dissipation	T _a =25°C	1.2	W
		T _C =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =50mA; I _B =5mA		0.12	0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =50mA; I _B =5mA		0.8	1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =180V; I _E =0			1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =3V; I _C =0			1	μA
h _{FE-1}	DC current gain	I _C =1mA; V _{CE} =5V	90	190		
h _{FE-2}	DC current gain	I _C =10mA; V _{CE} =5V	100	200	320	
f _T	Transition frequency	I _C =20mA; V _{CE} =10V		200		MHz
C _{ob}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz		3.2		pF

◆ h_{FE-2} Classifications

Q	P
100-200	160-320

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PACKAGE OUTLINE

